

Features

- Low on resistance
- Low gate charge
- Fast switching
- High avalanche current
- Low reverse transfer capacitances

Application

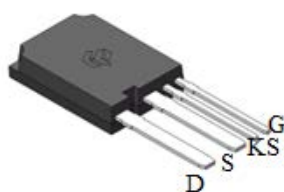
- Brushed and BLDC Motor drive systems
- Battery Management
- DC/DC and AC/DC Converter
- UPS

Product Summary

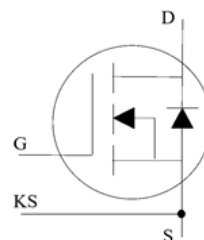
V_{DS}	100V
$R_{DS(on)}$ typ.	1.5mΩ
I_D (Silicon Limited)	420A
I_D (Package Limited)	280A

100% DVDS Tested

100% Avalanche Tested



SFG019N100C3



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
SFG019N100C3	019N100C3	TO-247PLUS-4L	Tube	N/A	N/A	30pcs

Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	100	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25^{\circ}\text{C}$ (Package Limited)	I_D	280	A
	$T_C = 25^{\circ}\text{C}$ (Silicon Limited)		420	
	$T_C = 100^{\circ}\text{C}$ (Silicon Limited)		316	
Pulsed Drain Current($T_C=25^{\circ}\text{C}$, t_p limited by T_{jmax})		$I_{D,Pulse}$	1120	A
Single Pulsed Avalanche Energy($L=0.5\text{mH}$, $V_{DD}=80\text{V}$, $T_J=25^{\circ}\text{C}$)		E_{AS}	1350	mJ
Power Dissipation	$T_C = 25^{\circ}\text{C}$	P_{tot}	480	W
Junction Temperature		T_J	-55 ~ 150	°C
Storage Temperature		T_{STG}	-55 ~ 150	°C

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance , junction – case	R_{thJC}	0.26	°C/W
Thermal resistance , junction – ambient(min. footprint)	R_{thJA}	34	°C/W

Electrical Characteristics ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
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Static Characteristics

Drain - Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$ $T_C = 25^{\circ}\text{C}$ $T_C = 125^{\circ}\text{C}$	- - -	- - -	5 100	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	-	4	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 90A$	-	1.5	1.9	mΩ

Dynamic Characteristics

Input Capacitance	C_{iss}	$V_{DS} = 50V, V_{GS} = 0V, f = 1\text{MHz}$	-	22000	-	pF
Output Capacitance	C_{oss}		-	2800	-	
Reverse Transfer Capacitance	C_{rss}		-	105	-	
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$	-	2.4	-	Ω

Switching Characteristics

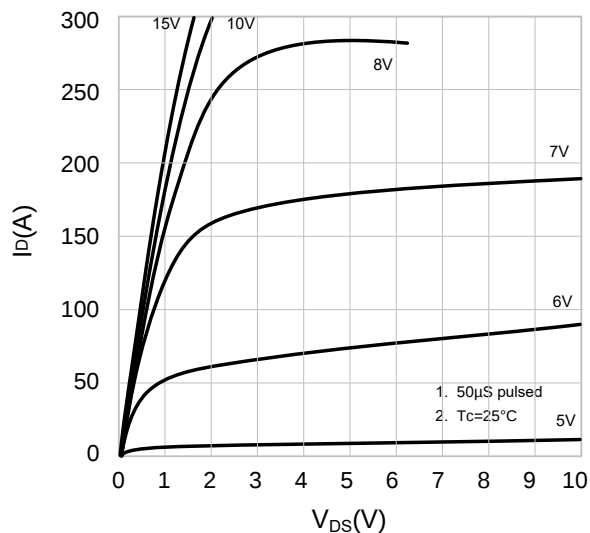
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V, I_D = 90A$	-	268	-	nC
Gate-source Charge	Q_{gs}		-	116	-	
Gate-drain Charge	Q_{gd}		-	85	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50V, V_{GS} = 10V, I_D = 90A,$ $R_G = 3\Omega$	-	60	-	ns
Turn-on Rise Time	t_r		-	108	-	
Turn-off Delay Ttime	$t_{d(off)}$		-	162	-	
Turn-off Fall Time	t_f		-	93	-	

Body Diode Characteristic

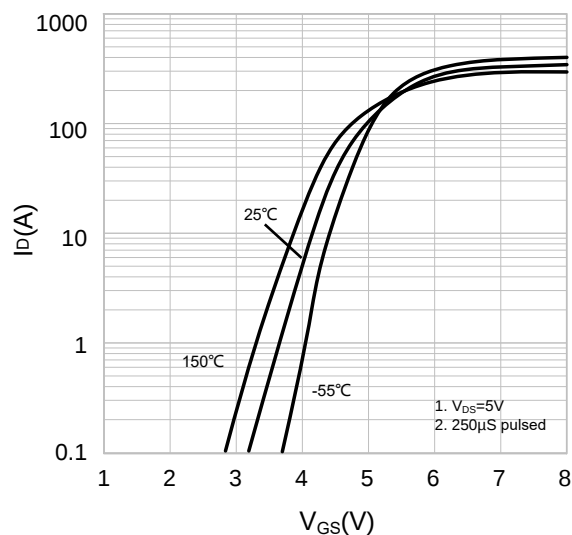
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Body Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_{SD} = 90A$	-	-	1.4	V
Body Diode Reverse Recovery Time	T_{rr}	$I_F = 90A, di/dt = 100A/\mu s$	-	124	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 90A, di/dt = 100A/\mu s$	-	320	-	nC

Typical Performance Characteristics

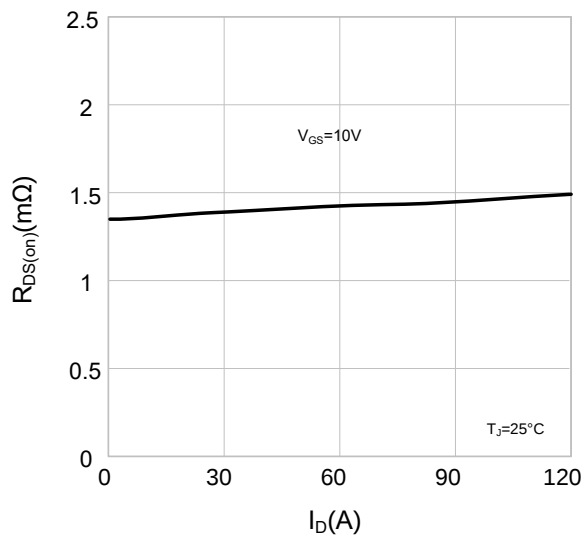
Output Characteristics



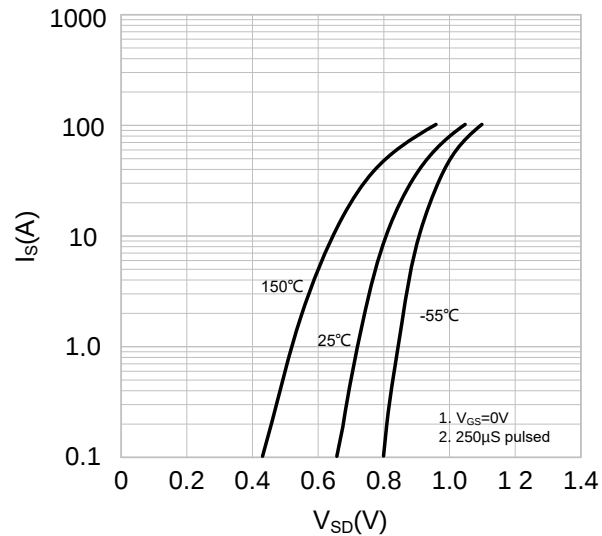
Transfer Characteristics



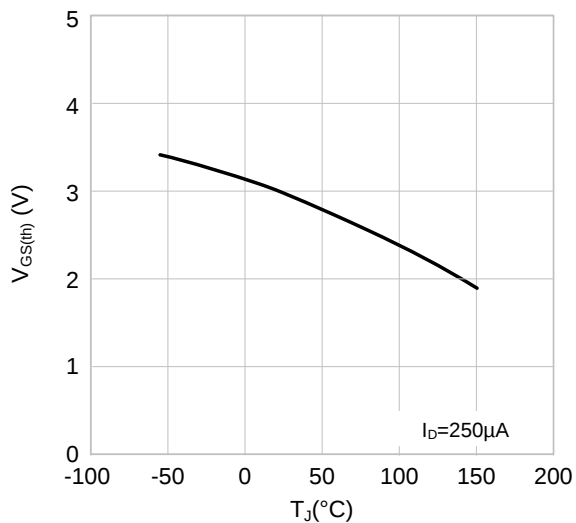
$R_{DS(on)}$ vs Drain Current



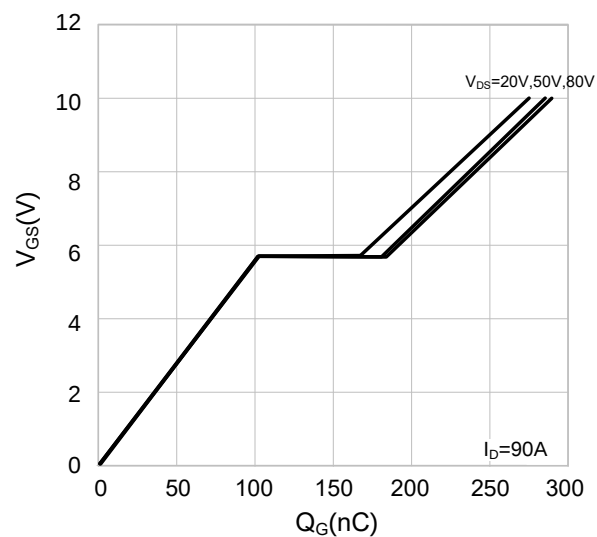
Body-diode Forward Characteristics



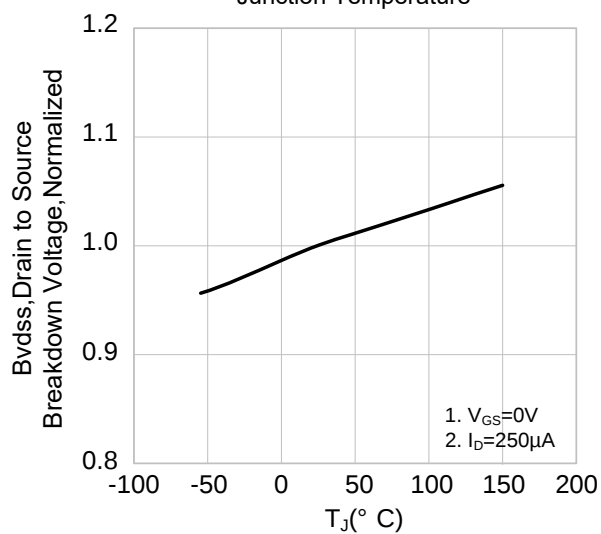
$V_{GS(th)}$ vs T_J



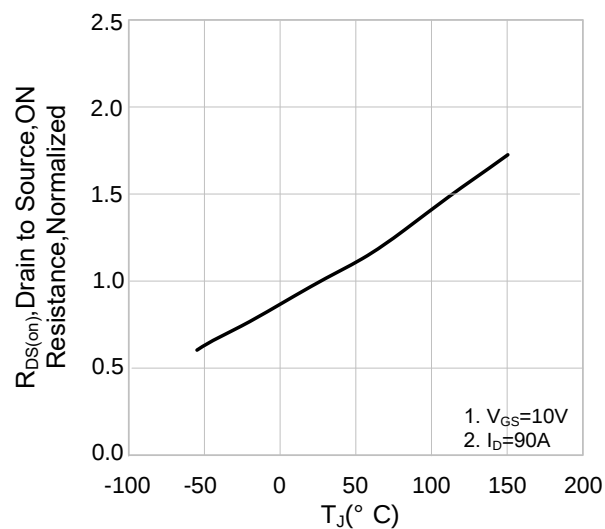
Gate Charge Characteristics



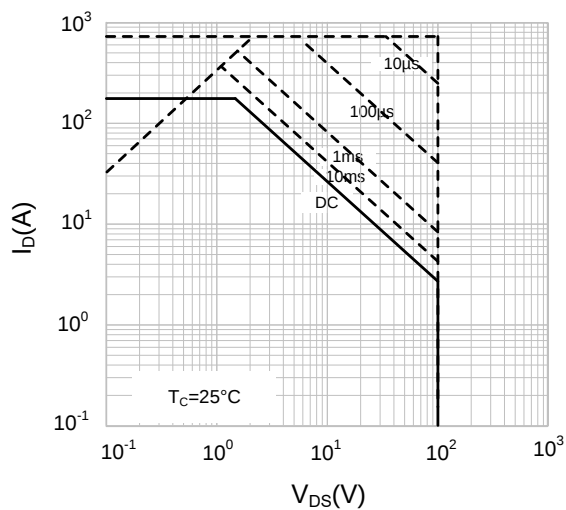
Typical Breakdown Voltage vs
Junction Temperature



$R_{DS(on)}$ vs. Temperature

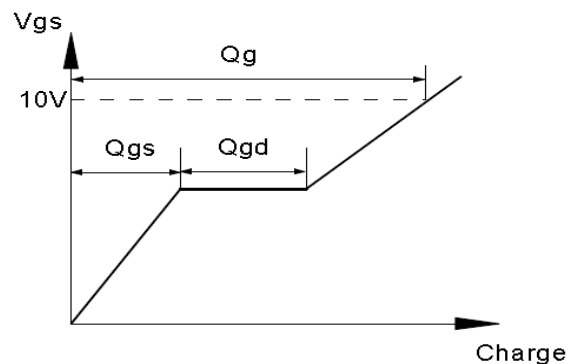
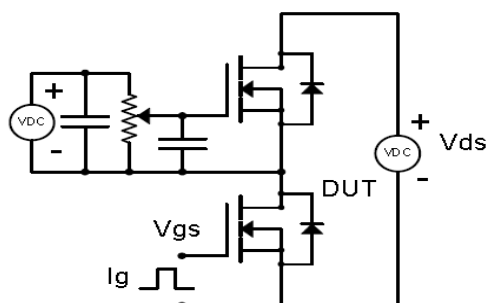


Safe Operating Area

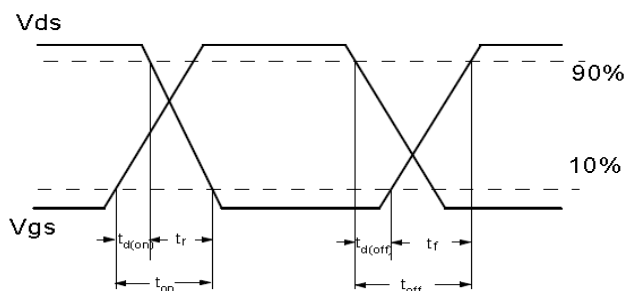
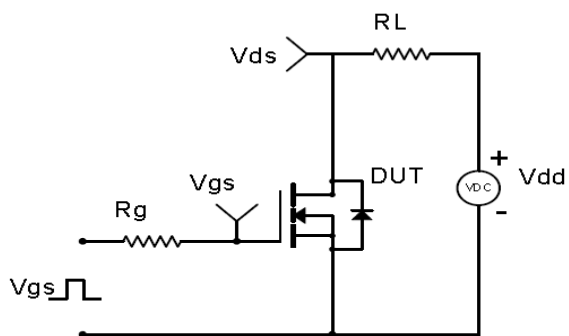


Test Circuit & Waveform

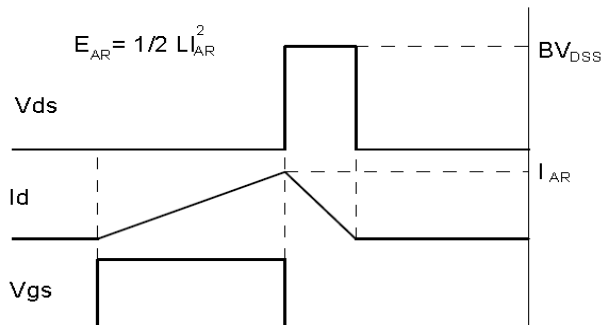
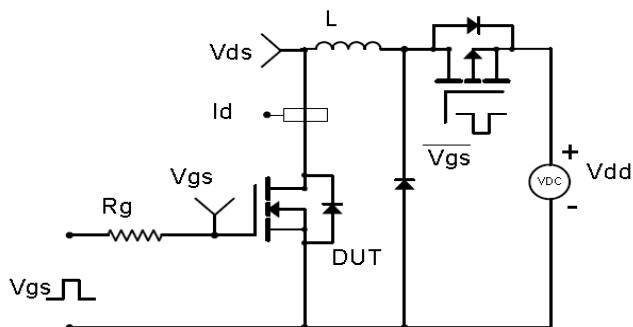
Gate Charge Test Circuit & Waveform



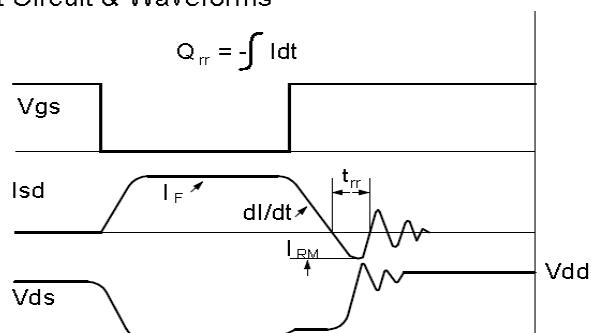
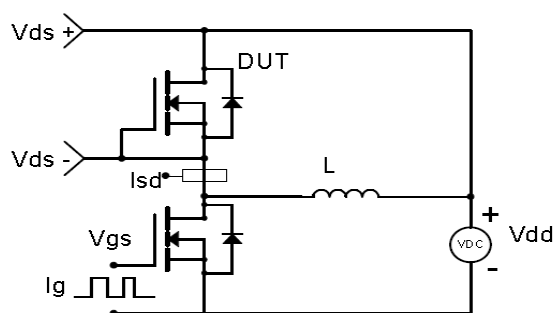
Resistive Switching Test Circuit & Waveforms

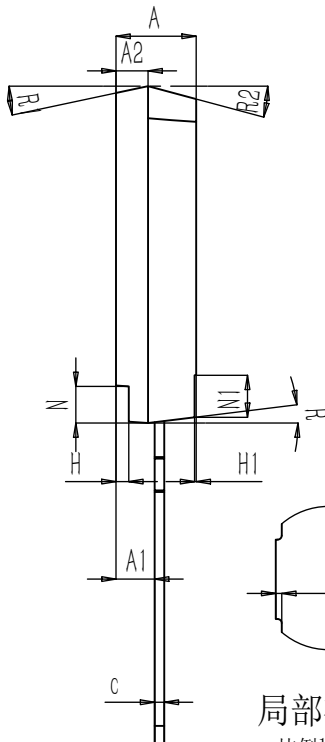
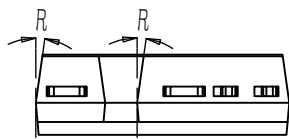
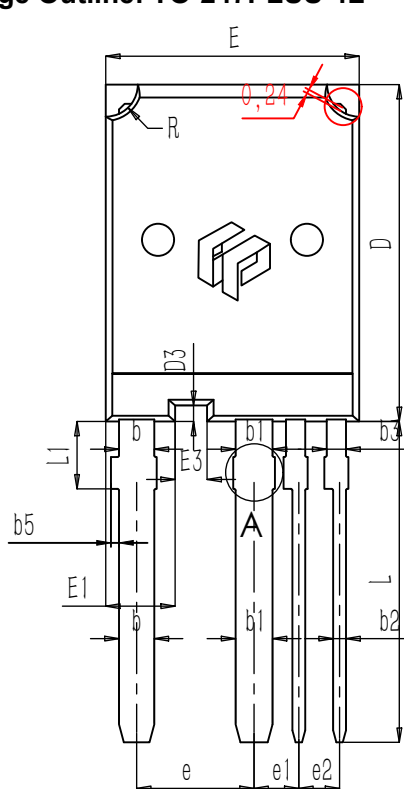


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

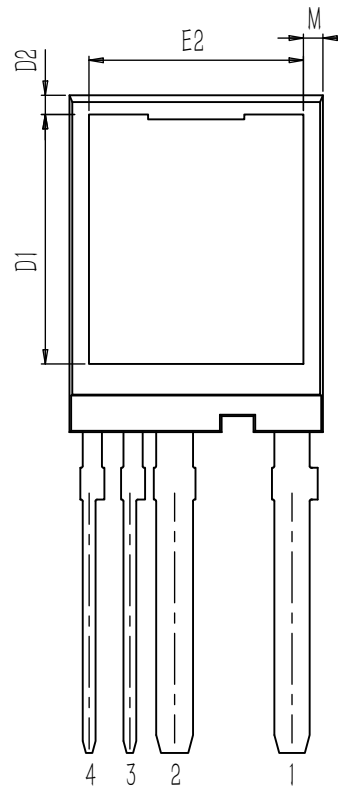


Diode Recovery Test Circuit & Waveforms



Package Outline: TO-247PLUS-4L


局部视图 A
比例 10 : 1



DIMENSION	MILLIMETERS		
	MIN	NOM	MAX
A	4.95	5	5.05
A1	2.36	2.41	2.46
A2	1.95	2	2.05
b	2.15	2.2	2.25
b1	2.25	2.3	2.35
b2	0.75	0.8	0.85
b3	1.15	1.2	1.25
b4	MAX0.075		
b5	0.45	0.5	0.55
c	0.595	0.6	0.635
D	20.9	21	21.1
D1	15.05	15.55	16.05
D2	1.15	1.2	1.25
D3	0.95	1	1.05
E	15.75	15.8	16.85
E1	4.2	4.33	4.4
E2	13.3	13.37	13.5
E3	1.95	2	2.05
e	7.32		
e1	2.79		
e2	2.54		
H	0.75	0.8	0.85
H1	0.05	0.1	0.15
L	19.9	20	20.1
L1	4.1	4.2	4.3
M	1.17	1.22	1.27
N	2.2	2.3	2.4
N1	2.5	2.6	2.7
R	1.9	2	2.1
S	8°		
S1	12°		
S2	15°		

Revision History

Revision	Date	Major Changes
1.0	2023-5-26	Release of formal version
1.1	2023-6-15	Update Characteristics

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

Scilicon Electric reserves the right to improve product design, function and reliability without notice.